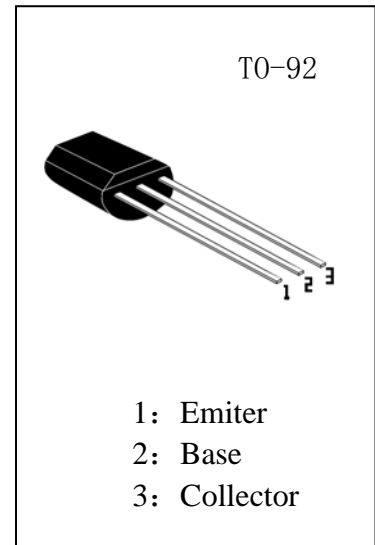


高压晶体管

- $V_{ce}=-400V$
- 低饱和电压
- 与 MPSA44 对管

极限参数(Absolute Maximum Ratings) $T_a=25^{\circ}C$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	-400	V
Collector-Emitter Voltage	V_{ceo}	-400	V
Emitter-Base Voltage	V_{ebo}	-6	V
Collector Current	I_c	-300	mA
Collector Dissipation	P_c	625	m W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~150	$^{\circ}C$



电性能(Electrical Characteristic) $T_a=25^{\circ}C$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c=-100\mu A$ $I_e=0$	-400			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c=-1mA$ $I_b=0$	-400			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e=-100\mu A$ $I_c=0$	-6			V
I_{cbo}	Collector Cutoff Current	$V_{cb}=-300V$, $I_e=0$			-100	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb}=-4V$, $I_c=0$			-100	nA
I_{ces}	Collector Cutoff Current	$V_{ce}=-400V$, $V_{eb}=0$			-1	μA
$V_{ce(sat)1}$	Collector-Emitter Saturation Voltage	$I_c=-10mA$, $I_b=-1mA$			-0.5	V
$V_{ce(sat)2}$	Collector-Emitter Saturation Voltage	$I_c=-50mA$, $I_b=-5mA$			-0.75	V
$V_{be(sat)}$	Base-Emitter Saturation Voltage	$I_c=-10mA$, $I_b=-1mA$			-0.75	V
H_{fe1}	DC Current Gain	$V_{ce}=-10V$, $I_c=-1mA$	40			
H_{fe2}	DC Current Gain	$V_{ce}=-10V$, $I_c=-10mA$	50		300	
H_{fe3}	DC Current Gain	$V_{ce}=-10V$, $I_c=-50mA$	45			
H_{fe4}	DC Current Gain	$V_{ce}=-10V$, $I_c=-100mA$	40			
C_{ob}	Output Capacitance	$V_{cb}=-20V$, $I_e=0$, $f=1MHz$			7	PF
f_T	Current Gain-Bandwidth product	$V_{ce}=-20V$, $I_c=-10mA$	50			MHz

Class	B	C	D	E
Hfe2	50-80	80-150	150-200	200-300